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2.COLLECTOR 3.EMITTER

TO-220Fa package

PIN 1. BASE

123

isc Silicon NPN Power Transistor

2SC3709A

DESCRIPTION

- Low Collector Saturation Voltage-
- : V_{CE(sat)}= 0.4V(Max)@I_C= 6A
- Good Linearity of h_{FE}
- Complement to Type 2SA1451A

APPLICATIONS

Designed for high current switching applications

ABSOLU [.]	TE MAXIMUM RATINGS(Ta=2	5°C)			3	→ s	•	
SYMBOL	PARAMETER	VALUE	UNIT		$\overline{)}$			Ø_
V _{СВО}	Collector-Base Voltage	60	v		-•-			TTTTTT
V _{CEO}	Collector-Emitter Voltage	50	v	ĸ				
Vebo	Emitter-Base Voltage	6	v		ļļ		₹_J	
lc	Collector Current-Continuous	12	A			-C m	n n	⊸ N►
I _{CP} *	Pulse Collector Current	30	A		DIM A B	MIN 16.85 9.54	MAX 17.15 10.10	
I _B	Base Current-Continuous	2	A		C D F G	4.35 0.75 3.20 6.90	4.65 0.90 3.40 7.20	-
Pc	Collector Power Dissipation @ T _C =25°C	30	w		H J K	5.15 0.45 13.35 1.10	5.45 0.75 13.65 1.30	-
TJ	Junction Temperature	150	°C		N Q R	4.98 4.85 2.55	5.18 5.15 3.25	-
T _{stg}	Storage Temperature Range	-55~150	°C		S U V	2.70 1.75 1.30	2.90 2.05 1.50	

* Tested in QT-2 transistor graphic instrument and test condition is IB=2A,VCE=5V.

isc website: www.iscsemi.com 1



INCHANGE SEMICONDUCTOR

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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 50mA ; I _B = 0	50			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 0.3A			0.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 6A; I _B = 0.3A			1.2	V
Ісво	Collector Cutoff Current	V _{CB} = 60V; I _E = 0			10	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C = 0			10	μA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 1V	70		240	
h _{FE-2}	DC Current Gain	I _C = 6A; V _{CE} = 1V	40			
Сов	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1MHz		180		pF
f⊤	Current-Gain—Bandwidth Product	Ic= 1A; V _{CE} = 5V		90		MHz

Switching Times

ton	Turn-on Time				0.2	μ S
t _{stg}	Storage Time		I_{B1} = - I_{B2} = 0.3A, R_L = 5 Ω ; $V_{CC} \approx 30V$,		1.0	μ S
t _f	Fall Time				0.2	μ S
♦ h _{EE} ₄ (♦ hread Classifications					

0	Y				
70-140	120-240				

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